

Switching Diode, High Voltage, High Temperature

BASH19L Series

Features

- 175°C $T_{J(MAX)}$ – Rated for High Temperature, Mission Critical Applications
- NSV Prefixes for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Continuous Reverse Voltage BASH19 BASH20 BASH21	V_R	120 200 250	Vdc
Repetitive Peak Reverse Voltage BASH19 BASH20 BASH21	V_{RRM}	120 200 250	Vdc
Continuous Forward Current	I_F	200	mA dc
Peak Forward Surge Current (1/2 Cycle, Sine Wave, 60 Hz)	I_{FSM}	2	A
Repetitive Peak Forward Current (Pulse Train: $T_{ON} = 1$ s, $T_{OFF} = 0.5$ s)	I_{FRM}	0.6	A
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +175	°C
Electrostatic Discharge	ESD	HM < 500 MM < 400	V V

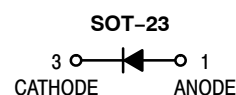
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



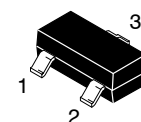
ON Semiconductor®

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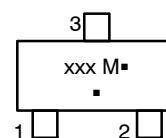
HIGH VOLTAGE SWITCHING DIODE



MARKING DIAGRAM



SOT-23 (TO-236)
CASE 318
STYLE 8



AD7 = BASH19L
AC7 = BASH20L
AA7 = BASH21L
M = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

BASH19L Series

THERMAL CHARACTERISTICS

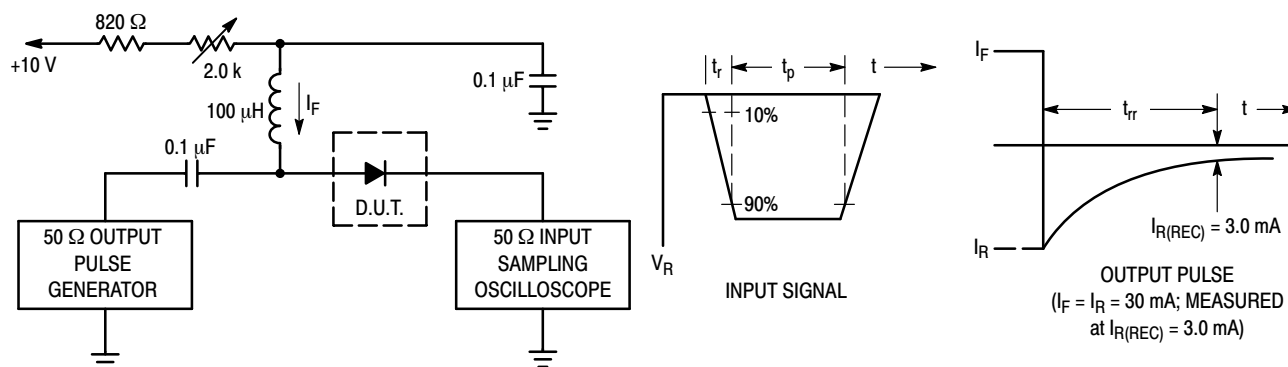
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300	mW
		1.8	mW/ $^\circ\text{C}$
Thermal Resistance Junction-to-Ambient (SOT-23)	$R_{\theta JA}$	340	$^\circ\text{C/W}$
Total Device Dissipation Alumina Substrate (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	400	mW
		2.4	mW/ $^\circ\text{C}$
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	250	$^\circ\text{C/W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +175	$^\circ\text{C}$

- FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Reverse Voltage Leakage Current ($V_R = 100$ Vdc) ($V_R = 150$ Vdc) ($V_R = 200$ Vdc) ($V_R = 100$ Vdc, $T_J = 175^\circ\text{C}$) ($V_R = 150$ Vdc, $T_J = 175^\circ\text{C}$) ($V_R = 200$ Vdc, $T_J = 175^\circ\text{C}$)	I_R BASH19 BASH20 BASH21 BASH19 BASH20 BASH21	– – – – – –	0.1 0.1 0.1 100 100 100	μA dc
Reverse Breakdown Voltage ($I_{BR} = 100$ μA dc) ($I_{BR} = 100$ μA dc) ($I_{BR} = 100$ μA dc)	$V_{(BR)}$ BASH19 BASH20 BASH21	120 200 250	– – –	Vdc
Forward Voltage ($I_F = 100$ mAdc) ($I_F = 200$ mAdc)	V_F	– –	1.0 1.25	Vdc
Diode Capacitance ($V_R = 0$, $f = 1.0$ MHz)	C_D	–	5.0	pF
Reverse Recovery Time ($I_F = I_R = 30$ mA, $I_{R(REC)} = 3.0$ mA, $R_L = 100$)	t_{rr}	–	50	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



- Notes: 1. A 2.0 k Ω variable resistor adjusted for a Forward Current (I_F) of 30 mA.
2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 30 mA.
3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

BASH19L Series

TYPICAL CHARACTERISTICS

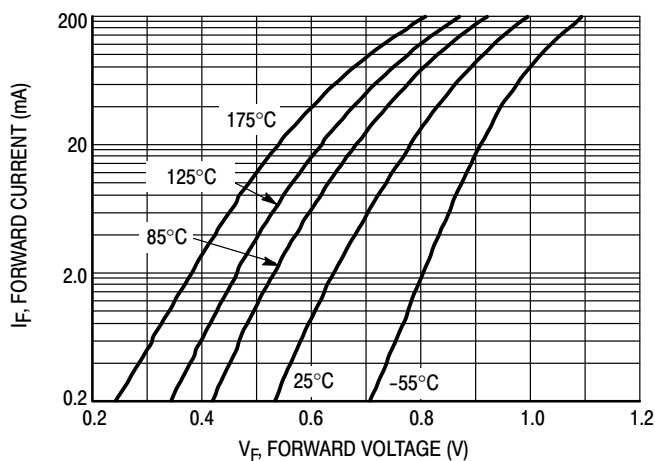


Figure 2. Forward Voltage

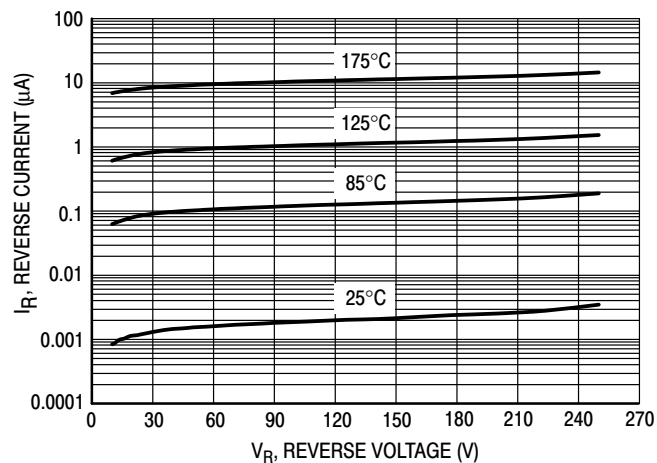


Figure 3. Leakage Current

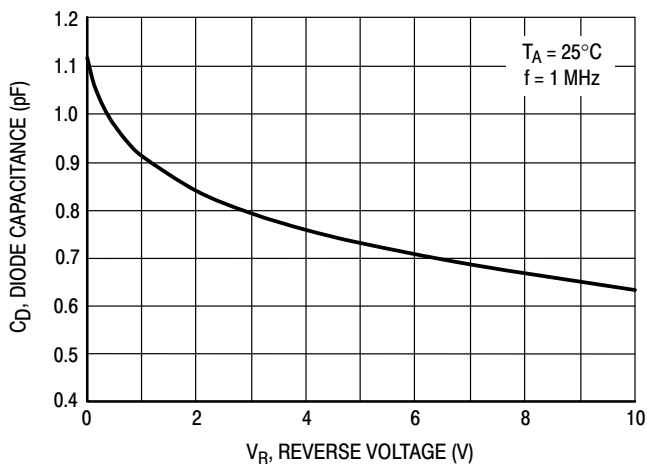


Figure 4. Capacitance

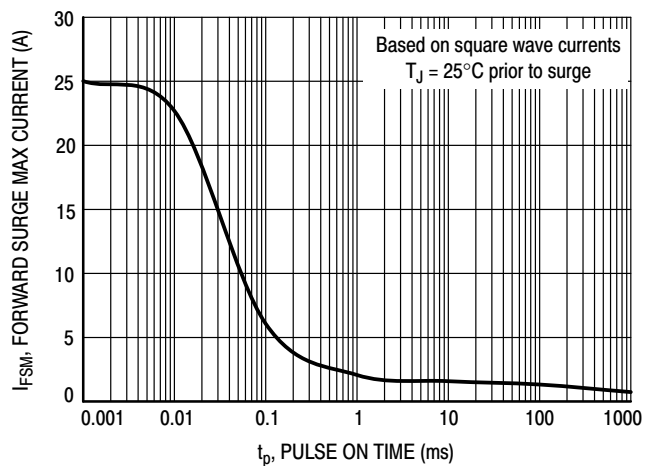


Figure 5. Forward Surge Current

BASH19L Series

ORDERING INFORMATION

Device	Package	Shipping†
BASH19LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
NSVBASH19LT1G*	SOT-23 (Pb-Free)	3000 / Tape & Reel
BASH20LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
NSVBASH20LT1G*	SOT-23 (Pb-Free)	3000 / Tape & Reel
BASH21LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
NSVBASH21LT1G*	SOT-23 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NSV Prefixes for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable – release available upon request.

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

ON Semiconductor®



SOT-23 (TO-236) CASE 318-08 ISSUE AS

DATE 30 JAN 2018

SCALE 4:1



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

RECOMMENDED SOLDERING FOOTPRINT



STYLE 1 THRU 5:
CANCELLED

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE-ANODE

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE

STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE

STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE

STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE

STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE-ANODE

STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT

STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE

STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION

STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE

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DESCRIPTION:	SOT-23 (TO-236)	PAGE 1 OF 1

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